



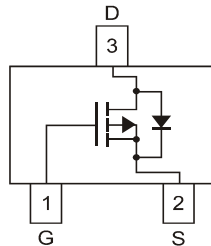
20V P-Channel Enhancement Mode MOSFET

FEATURES

- $R_{DS(ON)}$, $V_{GS}@-1.8V, I_D@-1.5A=200m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V, I_D@-2.2A=105m\Omega$
- Advanced Trench Process Technology
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SOT-23

Unit : inch(mm)



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	± 8	V
Continuous Drain Current (Notes 1)	Steady-State	I_D	$T_A=25^\circ\text{C}$	-1.75
	Steady-State		$T_A=70^\circ\text{C}$	-1.4
	$t \leq 5\text{s}$		$T_A=25^\circ\text{C}$	-2
Pulsed Drain Current (Notes 1)		I_{DM}	10	A
Power Dissipation (Notes 2)		P_D	$T_A=25^\circ\text{C}$	700
			$T_A=70^\circ\text{C}$	450
Typical Thermal Resistance (Notes 1)		$R_{\theta JA}$	175	$^\circ\text{C/W}$
Typical Thermal Resistance (Notes 1)		$R_{\theta JL}$	65	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to + 150	$^\circ\text{C}$

NOTES:

1. Mounted on minimum pad layout.
2. Mounted on 48cm^2 FR-4 PCB board.